RGW00TK65DGVC11

650V 50A Field Stop Trench IGBT

Datasheet

V _{CES}	650V
I _{C (100°C)}	26A
V _{CE(sat) (Typ.)}	1.5V@I _C =50A
P_D	89W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb free Lead Plating; RoHS Compliant

Applications

PFC

UPS

Welding

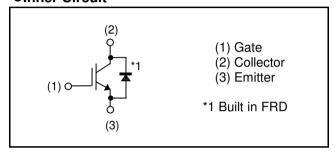
Solar Inverter

ΙH

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Typo	Tape Width (mm)	-
Type	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGW00TK65D

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	45	А
Collector Current	T _C = 100°C	I _C	26	А
Pulsed Collector Current		I _{CP} *1	200	А
Diode Forward Current	T _C = 25°C	I _F	34	А
	T _C = 100°C	I _F	19	А
Diode Pulsed Forward Current		I _{FP} *1	200	А
Power Dissipation	T _C = 25°C	P _D	89	W
	T _C = 100°C	P _D	44	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax}.

●Thermal Resistance

Parameter	Symbol	Values			Unit
Farameter		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	1.67	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	2.29	°C/W

ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	UTIIL
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_C = 10 \mu A, V_{GE} = 0 V$	650	1	-	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	1	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V$, $V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 33.0 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 50A$, $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.5 1.85	1.9 -	V

ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Davamatav	Cymphal	Conditions -	Values			Linit
Parameter	Symbol		Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	4200	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	104	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	79	-	
Total Gate Charge	Q_g	V _{CE} = 400V	-	141	-	
Gate - Emitter Charge	Q_{ge}	I _C = 50A	-	30	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	52	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 50A, V_{CC} = 400V$	-	52	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	21	-	
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	180	-	ns
Fall Time	t _f	Inductive Load	-	33	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	1.18	-	
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.96	-	mJ
Turn - on Delay Time	$t_{d(on)}$	$I_C = 50A, V_{CC} = 400V$	-	49	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	23	-	no
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	201	-	ns
Fall Time	t _f	Inductive Load	-	72	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	1.18	-	
Turn - off Switching Loss	E _{off}	reverse recovery	-	1.18	-	mJ
		$I_C = 200A, V_{CC} = 520V$				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
		$R_G = 100\Omega, T_j = 175^{\circ}C$				

●FRD Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Offic
Diode Forward Voltage	V_{F}	$I_F = 30A$ $T_j = 25$ °C $T_j = 175$ °C	-	1.45 1.55	1.9 -	V
Diode Reverse Recovery Time	t _{rr}	$I_F = 30A$ $V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 25^{\circ}C$	-	95	-	ns
Diode Peak Reverse Recovery Current	I _{rr}		1	8.1	-	A
Diode Reverse Recovery Charge	Q_{rr}		-	0.42	-	μC
Diode Reverse Recovery Energy	E _{rr}		-	19.3	-	μJ
Diode Reverse Recovery Time	t _{rr}	$I_F = 30A$ $V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 175^{\circ}C$	-	155	-	ns
Diode Peak Reverse Recovery Current	l _{rr}		1	10.4	1	Α
Diode Reverse Recovery Charge	Q_{rr}		-	0.95	-	μC
Diode Reverse Recovery Energy	E _{rr}		-	62.5	-	μJ

• Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

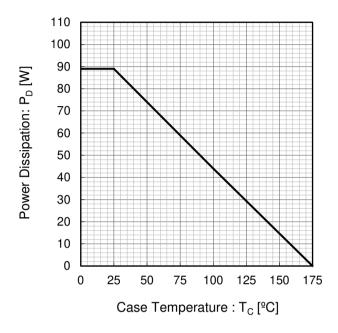


Fig.2 Collector Current vs. Case Temperature

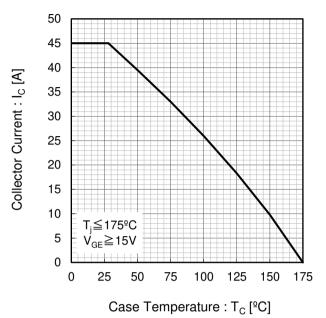


Fig.3 Forward Bias Safe Operating Area

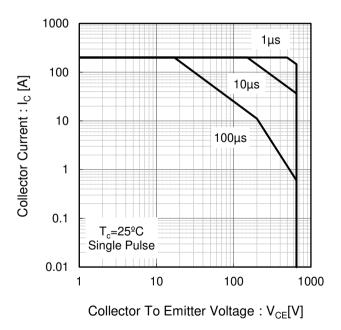
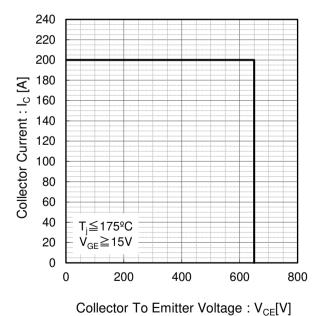


Fig.4 Reverse Bias Safe Operating Area



Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

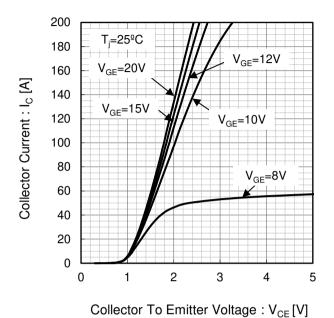
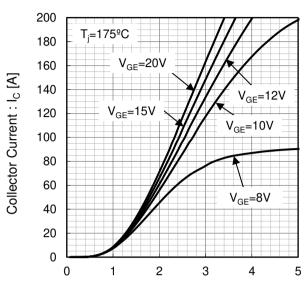


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : $V_{CE}[V]$

Fig.7 Typical Transfer Characteristics

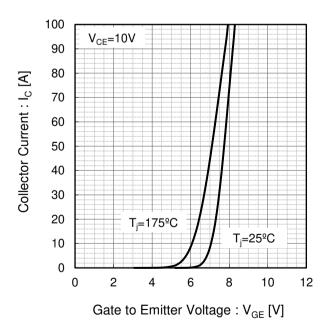
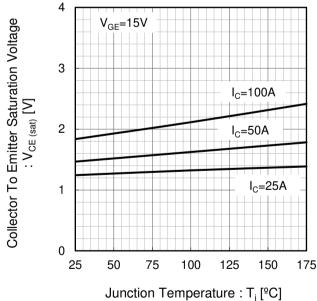
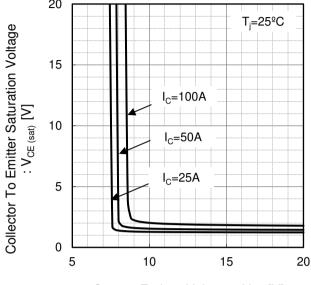


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



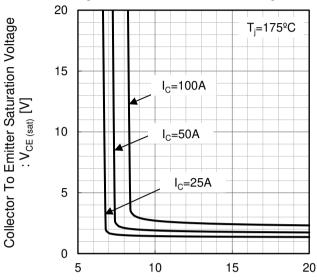
Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate to Emitter Voltage: V_{GE} [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate to Emitter Voltage: V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current

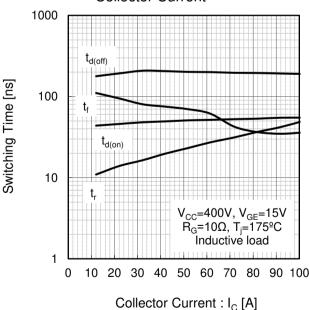
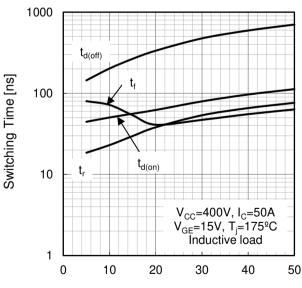


Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance : $R_G[\Omega]$

Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 0.1 V_{CC} =400V, V_{GE} =15V R_{G} =10 Ω , T_{j} =175 $^{\circ}$ C Inductive load 0.01 10 20 30 40 50 60 70 80 90 100

Collector Current : I_C [A]

Fig.14 Typical Switching Energy Losses vs. Gate Resistance 10 Switching Energy Losses [mJ] E_{off} 1 E_{on}

0.1

0.01

0

10

Gate Resistance : R_G [Ω]

30

20

Fig.16 Typical Gate Charge

 V_{CC} =400V, I_{C} =50A V_{GE} =15V, T_{j} =175 $^{\circ}$ C Inductive load

40

50

2022.04 - Rev.B

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz $V_{GE}=0V$ T_i=25ºC 0.1 0.01 1 10 100 Collector To Emitter Voltage : V_{CE}[V]

www.rohm.com

15 Gate to Emitter Voltage: VGE [V] 10 5 V_{CC}=400V $I_{C}=50A$ 0 20 40 60 80 100 120 140 160 0 Gate Charge : Q_a[nC]

8/11 © 2022 ROHM Co., Ltd. All rights reserved.

•Electrical Characteristic Curves

Fig.17 Typical Diode Forward Current vs. Forward Voltage 200 180 160 Forward Current : I_F [A] 140 120 100 T_i=25°C 80 60 T_i=175ºC 40 20 2 0 1 3 4 5 Forward Voltage: V_F[V]

Fig.18 Typical Diode Reverse Recovery Time
vs. Forward Current

400

SEL

100

T_j=175°C

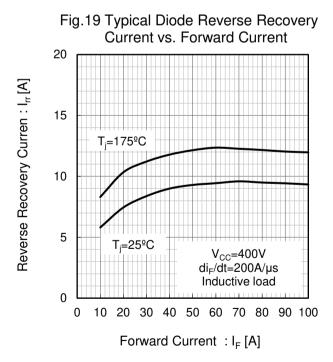
V_{CC}=400V

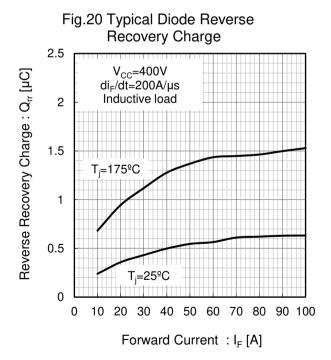
di_F/dt=200A/µs
Inductive load

0

10 20 30 40 50 60 70 80 90 100

Forward Current : I_F [A]





• Electrical Characteristic Curves

Fig.21 Typical IGBT Transient Thermal Impedance

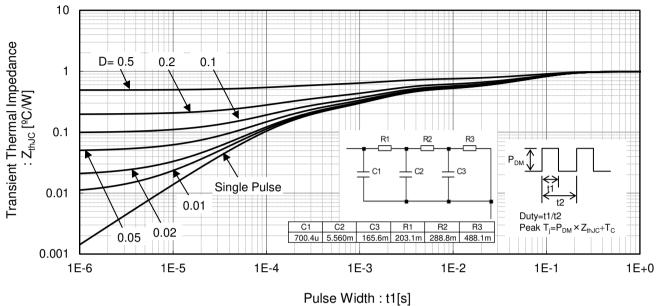
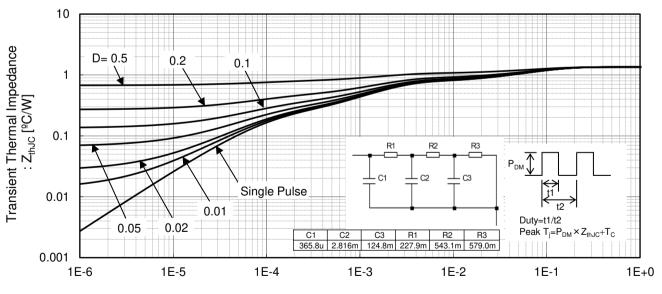


Fig.22 Typical Diode Transient Thermal Impedance



Pulse Width: t1[s]

•Inductive Load Switching Circuit and Waveform

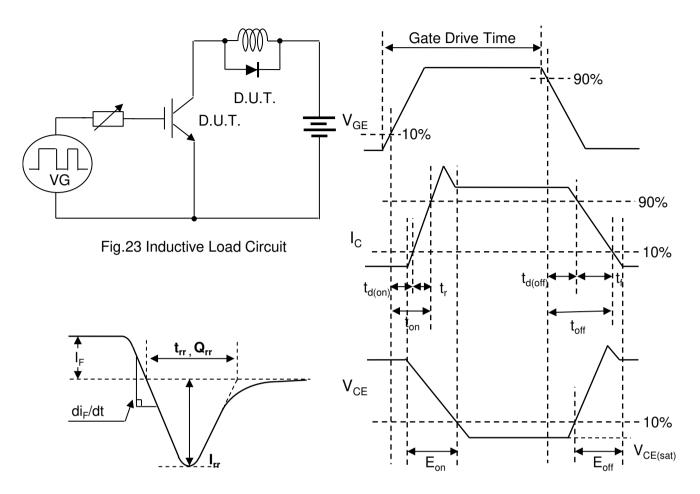


Fig.25 Diode Reverce Recovery Waveform

Fig.24 Inductive Load Waveform

Notes

- 1) The information contained herein is subject to change without notice.
- Before you use our Products, please contact our sales representative and verify the latest specifications
- 3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.

 Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.
- 4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.
- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
- 6) The Products specified in this document are not designed to be radiation tolerant.
- 7) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative: transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, and power transmission systems.
- 8) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
- 9) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
- 10) ROHM has used reasonable care to ensure the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
- 11) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
- 12) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
- 13) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/

General Precaution

- 1. Before you use our Products, you are requested to carefully read this document and fully understand its contents. ROHM shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any ROHM's Products against warning, caution or note contained in this document.
- 2. All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using ROHM's Products, please confirm the latest information with a ROHM sales representative.
- 3. The information contained in this document is provided on an "as is" basis and ROHM does not warrant that all information contained in this document is accurate and/or error-free. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties resulting from inaccuracy or errors of or concerning such information.

Notice – WE Rev.001